



# Highly Tunable Molecular Rectifier Realized by Interfacial Design in Molecular Heterojunction with Two-Dimensional Materials

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Korea Univ.

Jaeho Shin

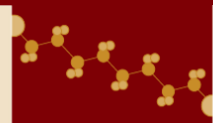
## Collaborators

Korea Univ. : Prof. C.-H. Lee (2D materials)

SNU: Prof. T. Lee (Transport Mechanism)

KIST: Dr. T.-W. Kim (Transport Mechanism)

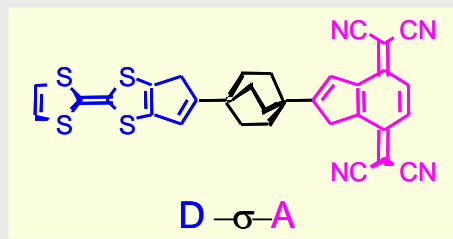




# Brief Introduction : Molecular Electronics (ME)

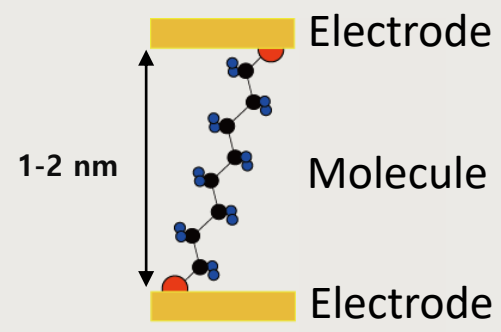
## Beginning of Molecular Electronics

“Donor-Acceptor” molecule acts as **P-N junction diode**



Aviram and M. Ratner, *Chem. Phys. Lett.* 29, 277 (1974)

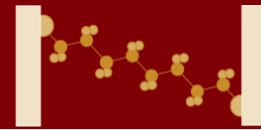
## Molecular Junction



## Development of ME

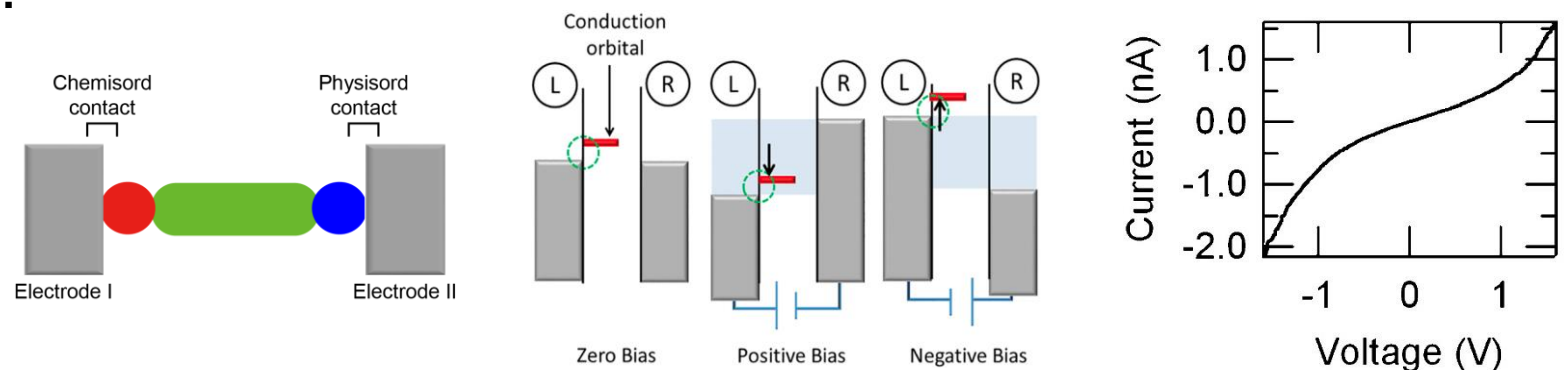


Advantages	Challenges
• Low cost & Low Temp.	• Synthesis of Functional Molecules
• Low energy & High Density	• Stability & Yield
• Molecular Functionalities	• Device Platform
• Self-Assembled Monolayer	• Integration/Addressability



# Previous Research: Molecular Rectifier

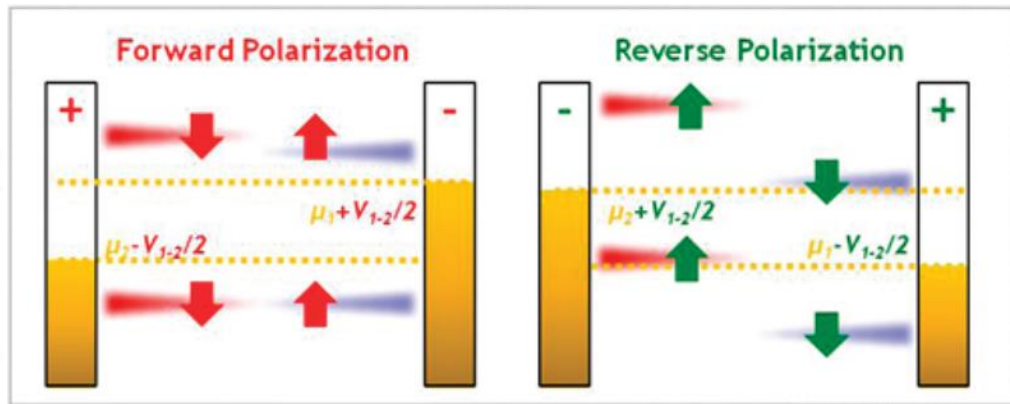
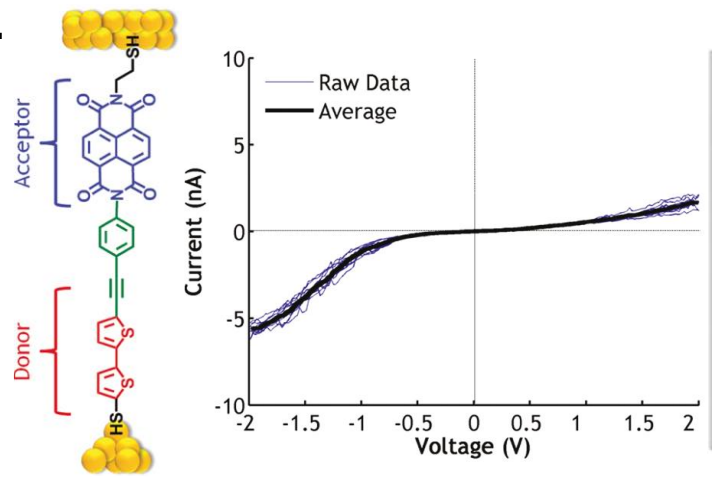
## Type 1.



- **Molecular-scale diode by using asymmetric molecule-metal coupling in the molecular junctions.**
- **Owing to the asymmetric molecule-metal coupling, the MO mainly follows the Fermi level of the one electrode.**
- **The average rectification ratio at a 1.5 V bias is about one.**

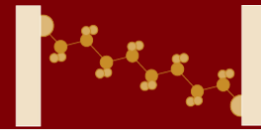
*ACS Nano*, 2, 827-832 (2008)  
*Sensors*, 17, 956 (2017)

## Type 2.



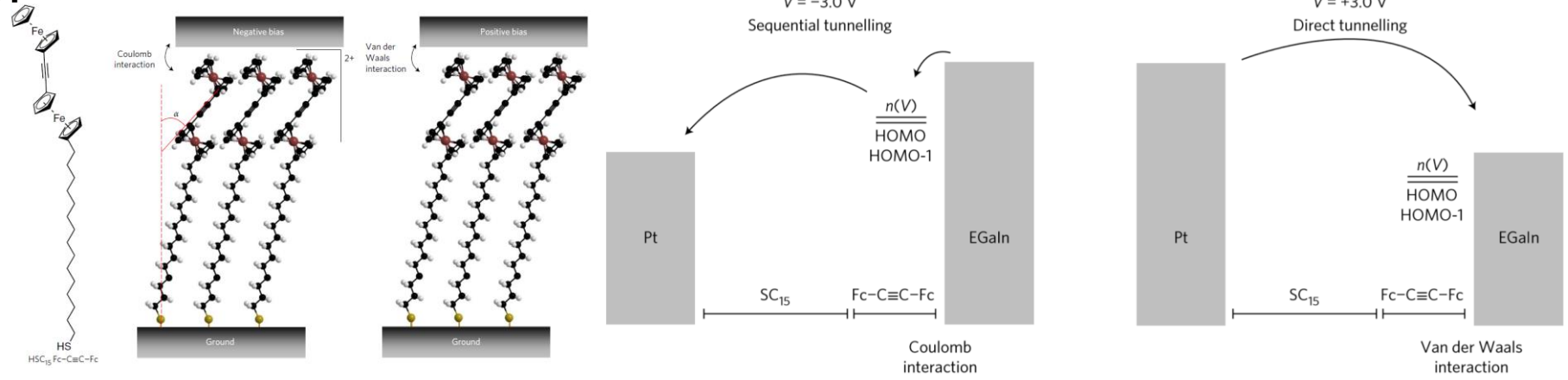
- **STM-BJ based molecular-scale diode, where an acceptor moiety covalently connected to a donor moiety.**
- **This molecular junctions resemble the Aviram-Ratner model molecule.**
- **The average rectification ratio at a 1.5 V bias is about five.**

*Nat. Chem.* 1, 635-641 (2009)  
*ACS Nano*, 5, 9256-9263 (2011)



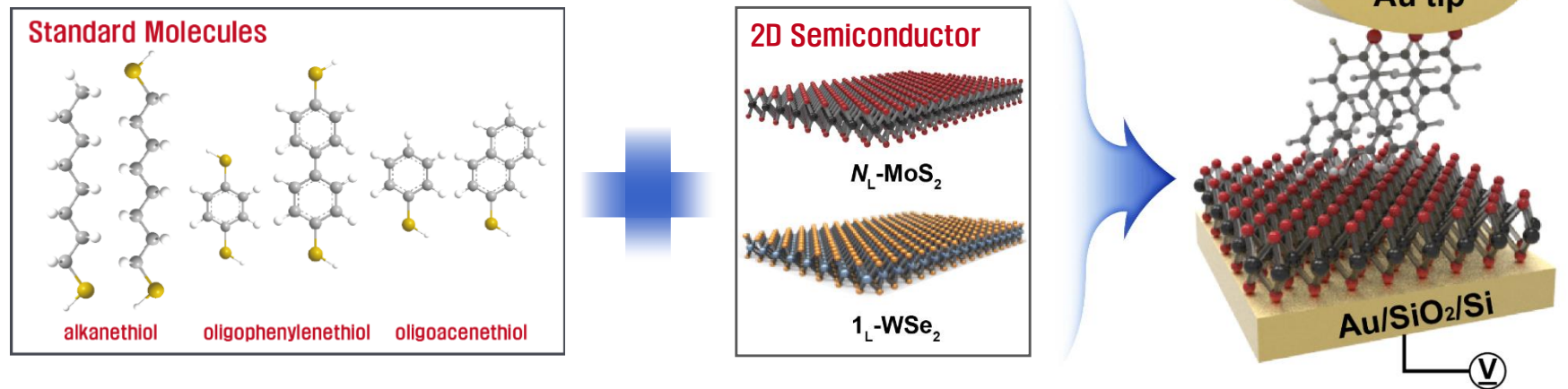
# Previous Research: Molecular Rectifier

## Type 3.

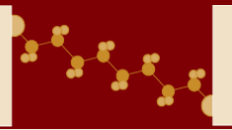


- **Two-level diode derived from EGaIn/SC<sub>15</sub>Fc-C≡C-Fc/Pt molecular junction.**
  - **Rectification ratio of  $6.3 \times 10^5$  which is the results of a mechanism of rectification based on an increase in the number of conducting molecules in only one direction of bias driven by electrostatic interactions.**
- Nat. Nanotech.* 12, 797-803 (2017)

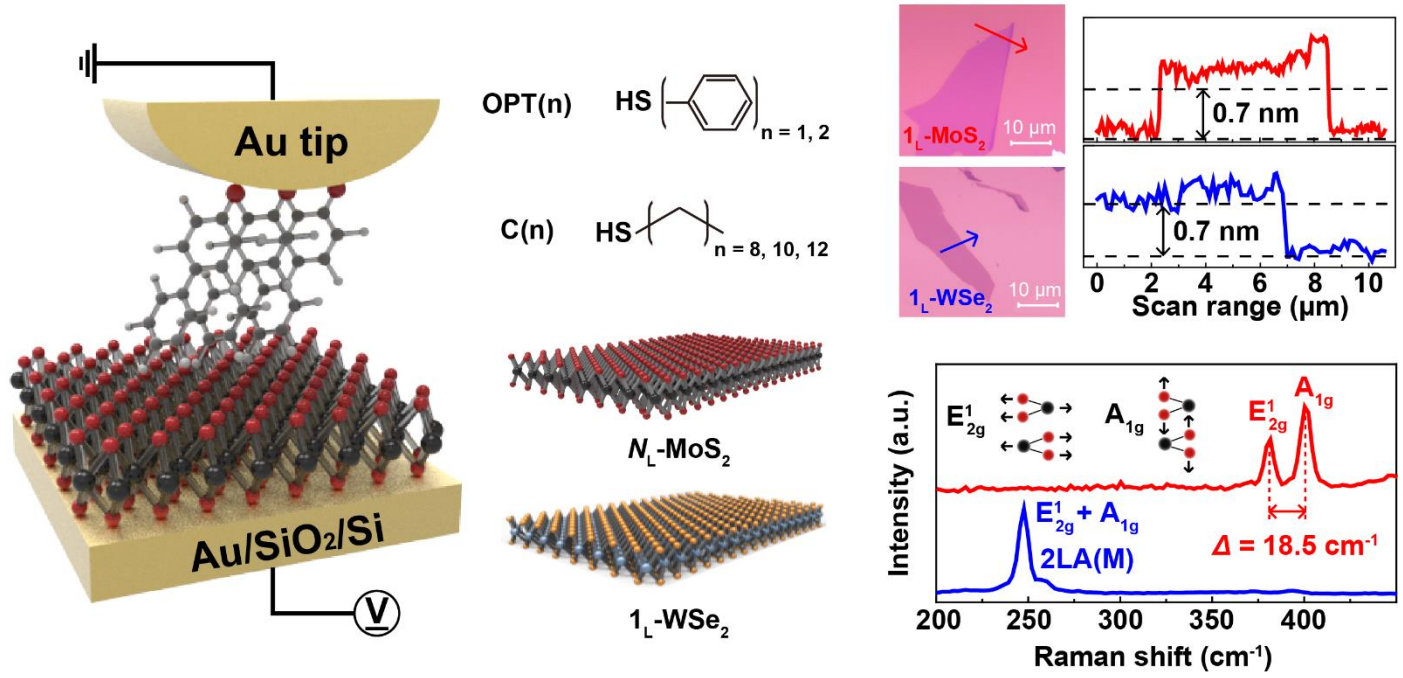
## Molecular heterojunction



J. Shin et al. *Nature Communication*, 11, 1412 (2020)



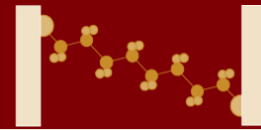
# Molecular Heterojunction System



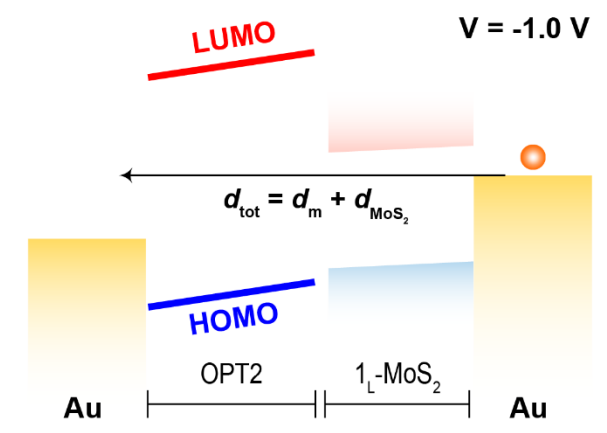
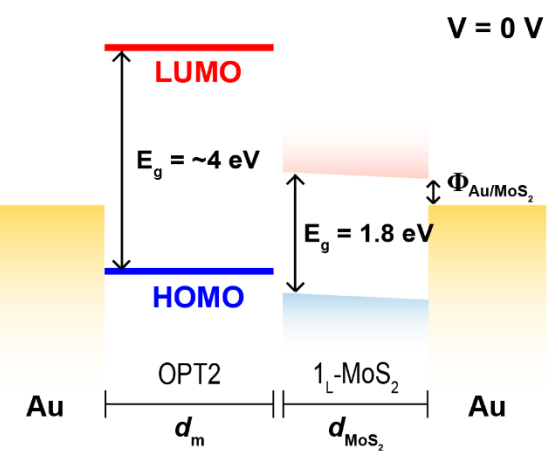
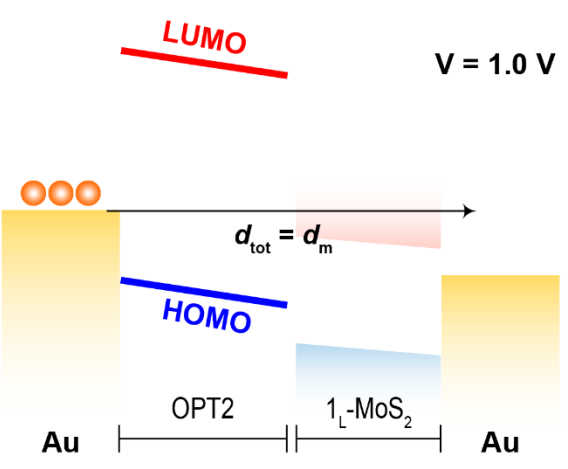
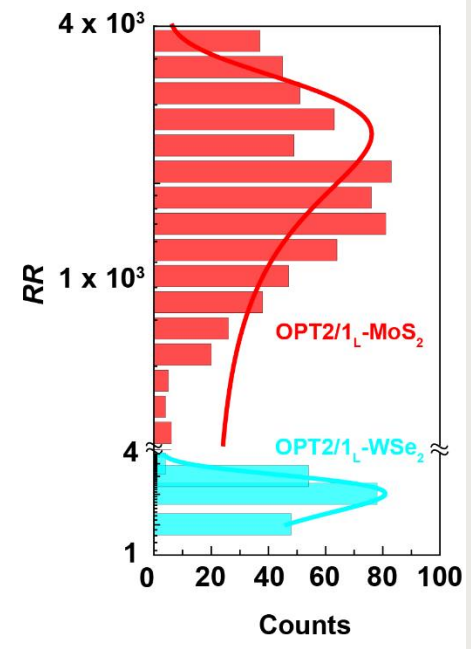
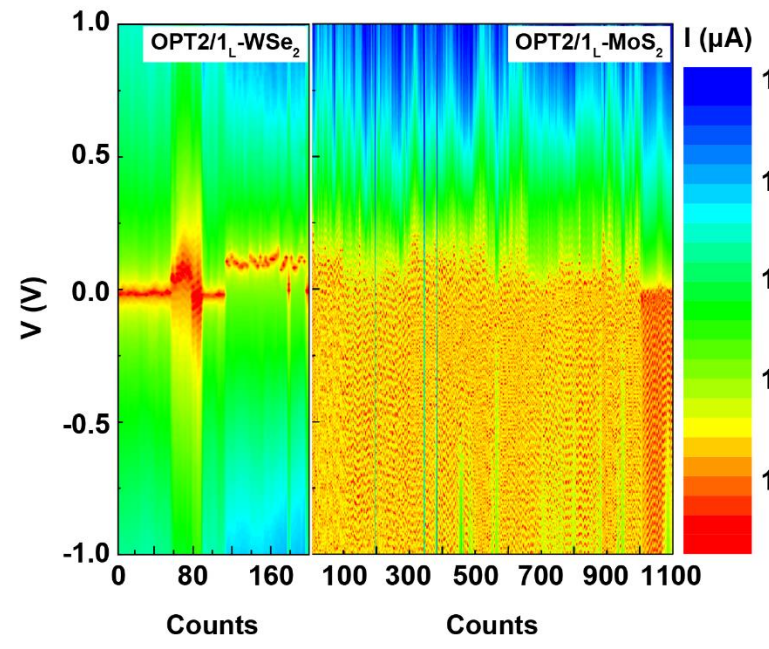
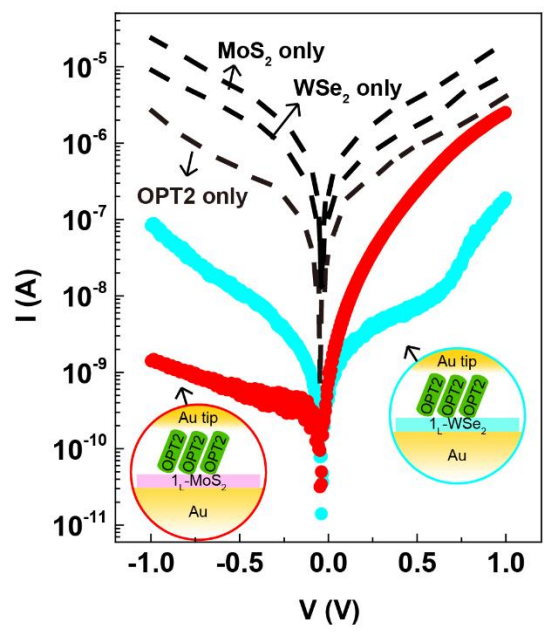
- Tip-loading force is set as 1 nN → To fix the interfacial coupling
- *n*-type MoS<sub>2</sub> / *p*-type WSe<sub>2</sub>
- Different HOMO-LUMO gap (alkyl- or conjugated-based)

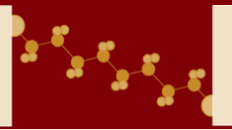


- I. Type of 2D semiconductor-dependence (MoS<sub>2</sub> or WSe<sub>2</sub>)
- II. Number of MoS<sub>2</sub> layers-dependence (1<sub>L</sub>-/2<sub>L</sub>-/3<sub>L</sub>-MoS<sub>2</sub>)
- III. Molecular length-dependence

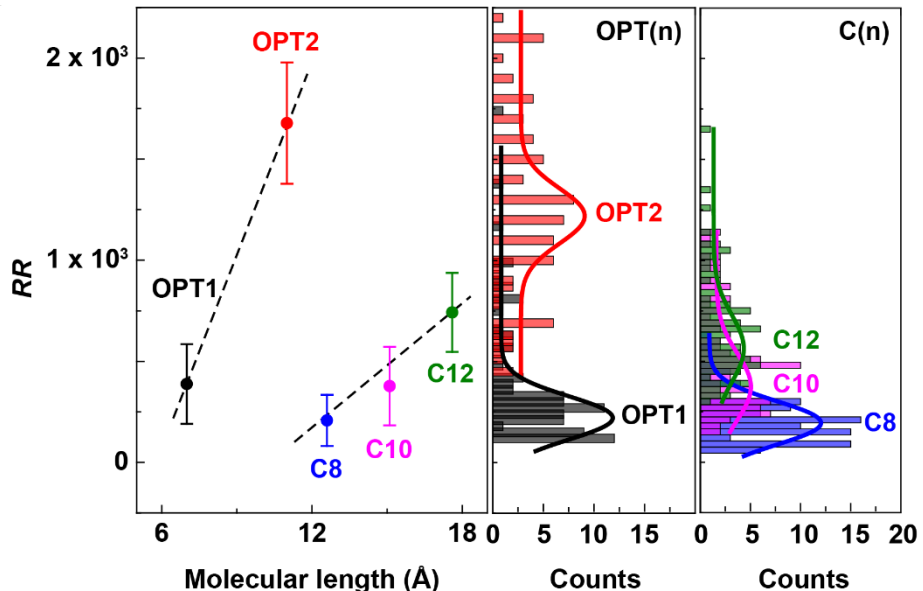
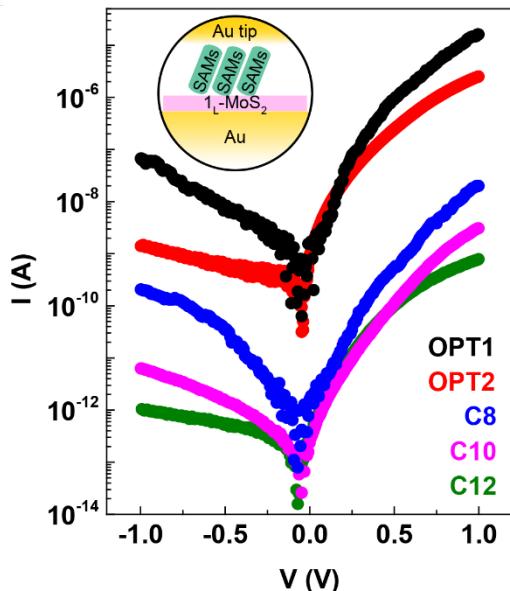
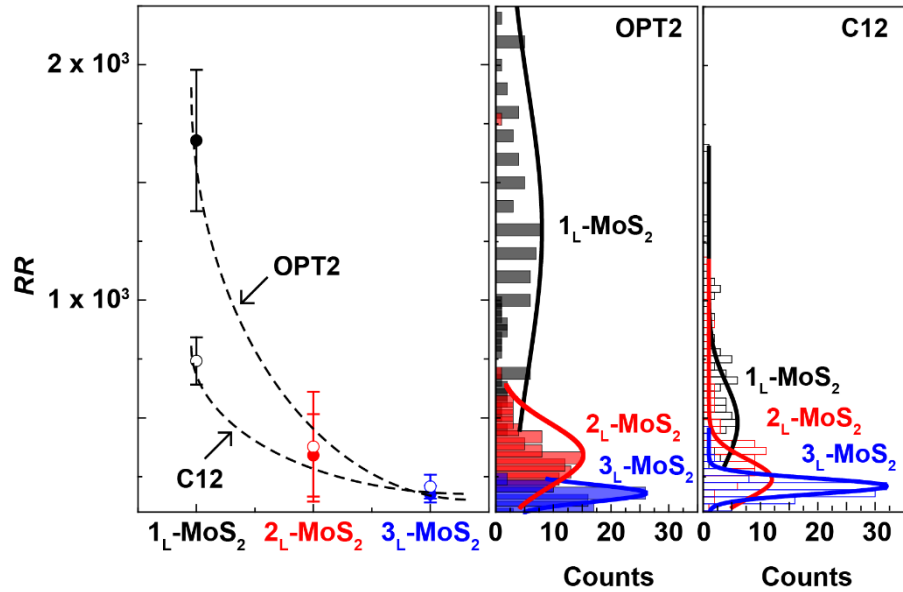
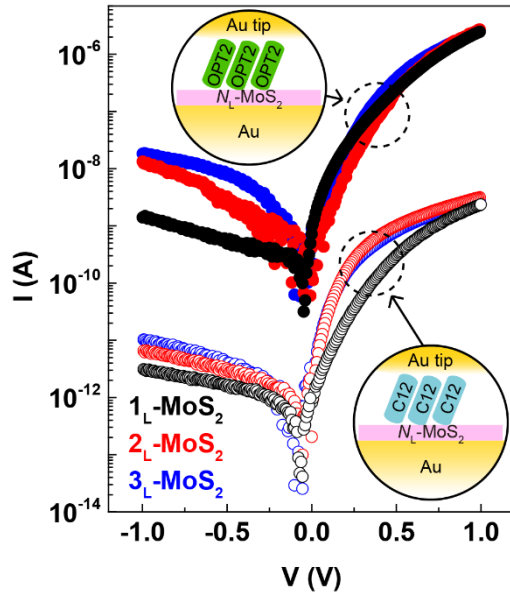


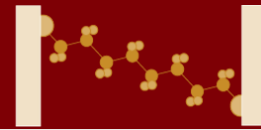
# Electrical Characteristics for Molecular Heterojunction



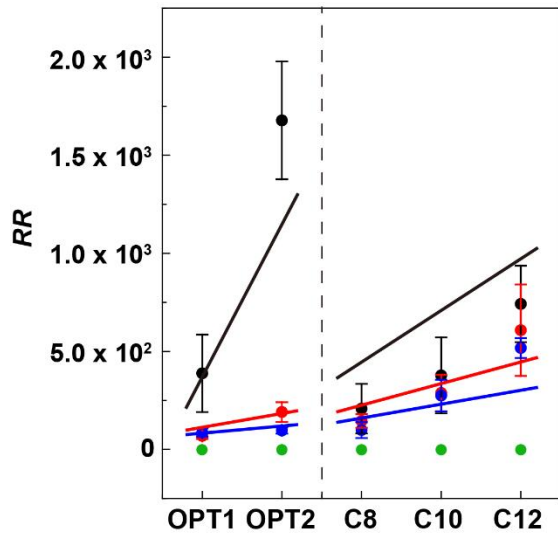
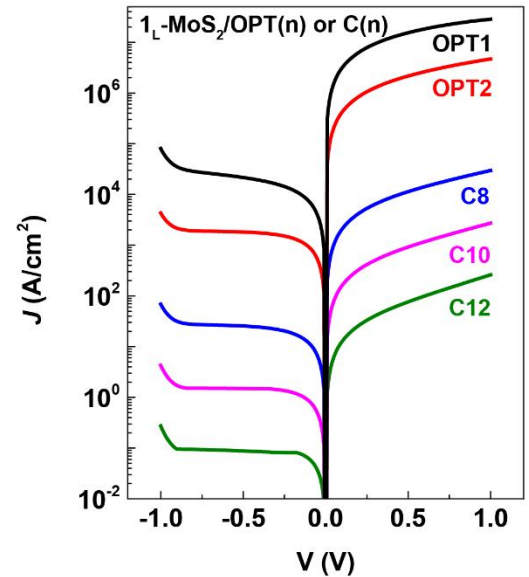


# Tunable Rectification of Molecular Heterojunction System

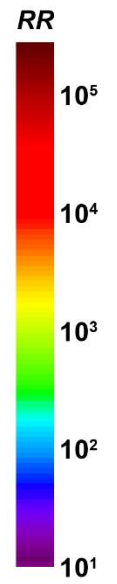
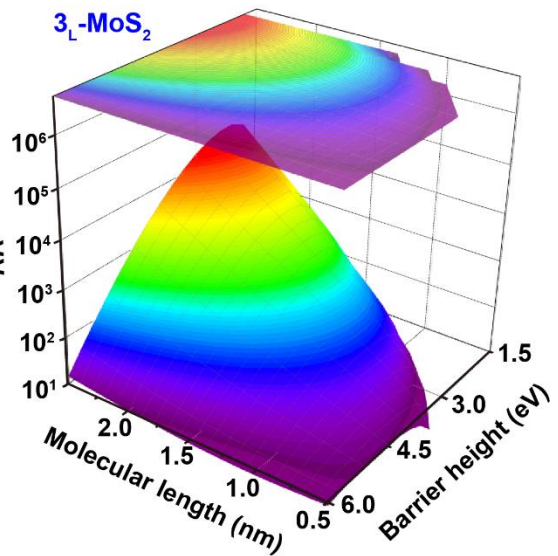
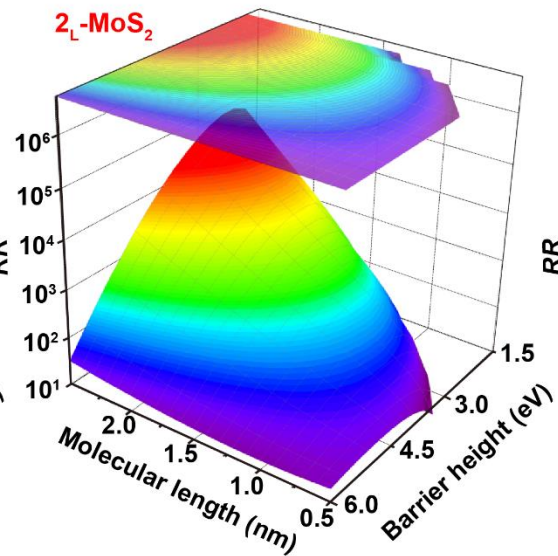
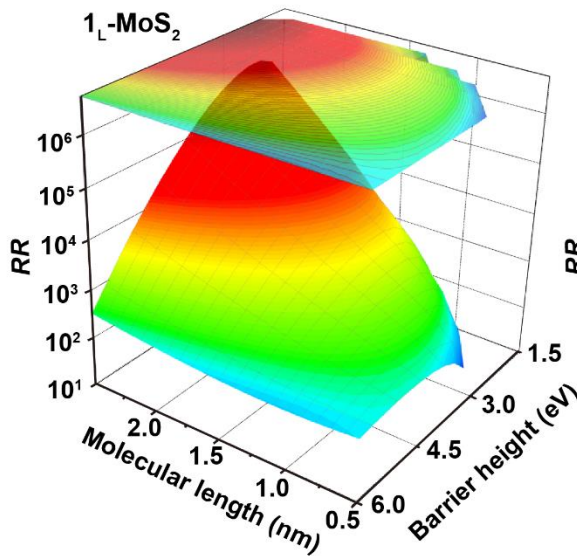




# Charge Transport Model

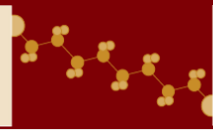


- Exp. values**
- OPT(n) or C(n)/1<sub>L</sub>-MoS<sub>2</sub>
  - OPT(n) or C(n)/2<sub>L</sub>-MoS<sub>2</sub>
  - OPT(n) or C(n)/3<sub>L</sub>-MoS<sub>2</sub>
- Theor. values**
- OPT(n) or C(n)/1<sub>L</sub>-MoS<sub>2</sub>
  - OPT(n) or C(n)/2<sub>L</sub>-MoS<sub>2</sub>
  - OPT(n) or C(n)/3<sub>L</sub>-MoS<sub>2</sub>
  - Other reported molecular junction w/o N<sub>L</sub>-MoS<sub>2</sub>



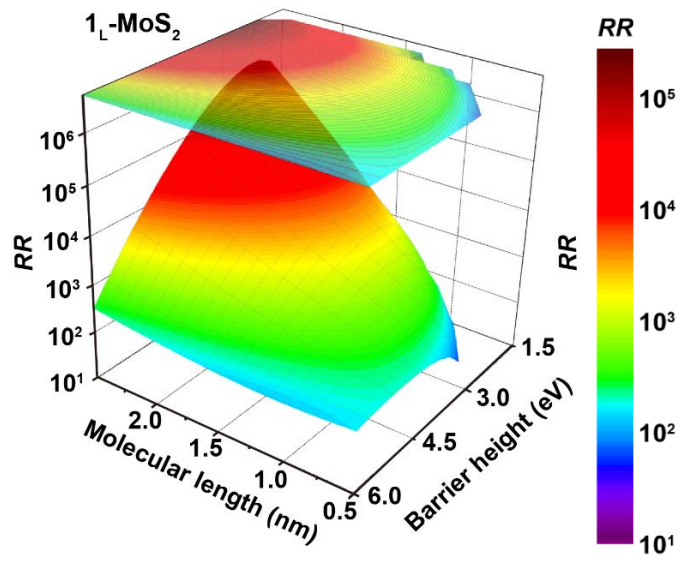
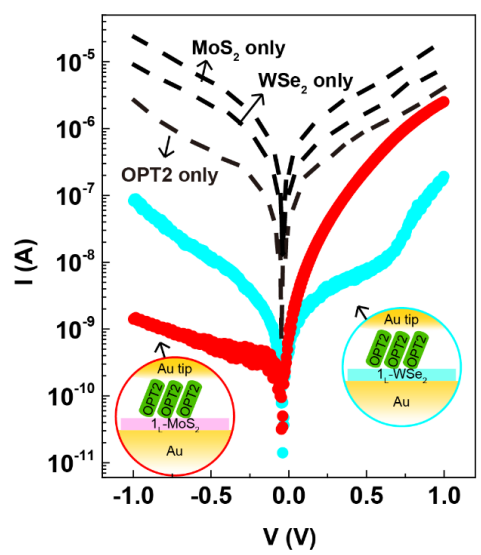
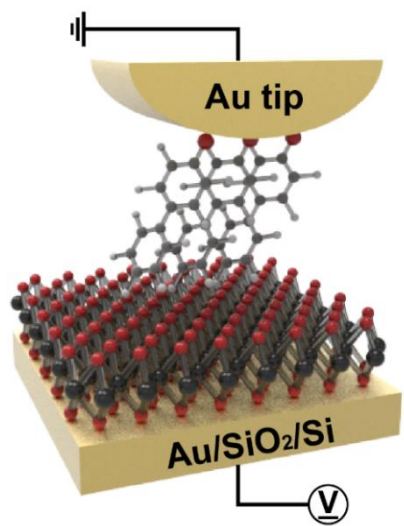
J. Shin et al. *Nature Communications* 11, 1412 (2020)





# Summary

## Conclusion



- We simply introduce a two-dimensional (2D) semiconductor ( $\text{MoS}_2$  and  $\text{WSe}_2$ ) as a rectifying designer at the alkyl or conjugated molecules/Au interface under 2 nm scale.
- These rectifying characteristics can be understood by the activation of different transport pathways depending on the voltage polarities through the different energy band alignments at junction interfaces.
- Notably, the rectifying characteristics can be largely tuned from  $2.46 \pm 1.42$  to  $(1.38 \pm 0.73) \times 10^3$  by changing the junction constituents such as molecular species, the type and number of 2D semiconductor layers.

J. Shin et al. *Nature Communications* 11, 1412 (2020)